

Alexander A Lebedev

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

357
papers

2,159
citations

19
h-index

35
g-index

376
ext. papers

2,390
ext. citations

1
avg, IF

5.03
L-index

#	Paper	IF	Citations
357	Prospects for the use of graphene-based biological sensors in the early diagnosis of Alzheimer's disease (review of literature).. <i>Klinicheskaya Laboratornaya Diagnostika</i> , 2022 , 67, 5-12	0.5	
356	Role of Low-Temperature Annealing in Modifying Silicon Carbide by Beams of Charged Particles. <i>Journal of Surface Investigation</i> , 2021 , 15, 341-344	0.5	0
355	Luminescence of structured InN deposited on graphene interlayer. <i>Journal of Luminescence</i> , 2021 , 232, 117878	3.8	1
354	Graphene on SiC Substrate as Biosensor: Theoretical Background, Preparation, and Characterization. <i>Materials</i> , 2021 , 14,	3.5	5
353	Radiation Hardness of Silicon Carbide upon High-Temperature Electron and Proton Irradiation. <i>Materials</i> , 2021 , 14,	3.5	3
352	Impact of high temperature electron irradiation on characteristics of power SiC Schottky diodes. <i>Radiation Physics and Chemistry</i> , 2021 , 185, 109514	2.5	5
351	Effect of high temperature irradiation with 15 MeV protons on characteristics of power SiC Schottky diodes. <i>Solid-State Electronics</i> , 2021 , 181-182, 108009	1.7	3
350	Detection of lysine molecular ions in solution gated field effect transistors based on unmodified graphene. <i>Journal of Applied Physics</i> , 2020 , 128, 215302	2.5	1
349	Characteristics of Schottky Rectifier Diodes Based on Silicon Carbide at Elevated Temperatures. <i>Semiconductors</i> , 2020 , 54, 1624-1627	0.7	
348	Effect of Proton and Electron Irradiation on Current-Voltage Characteristics of Rectifying Diodes Based on 4H-SiC Structures with Schottky Barrier. <i>Materials Science Forum</i> , 2020 , 1004, 1081-1087	0.4	1
347	Comparative Results of Low Temperature Annealing of Lightly Doped N-Layers of Silicon Carbide Irradiated by Protons and Electrons. <i>Materials Science Forum</i> , 2020 , 1004, 231-236	0.4	2
346	Investigation of the Influence of Structural Defects on the PL Spectra in n-3C-SiC. <i>Materials Science Forum</i> , 2020 , 1004, 278-283	0.4	
345	Influence of the Proton Irradiation Temperature on the Characteristics of High-Power High-Voltage Silicon Carbide Schottky Diodes. <i>Technical Physics Letters</i> , 2020 , 46, 287-289	0.7	5
344	Intercalation Synthesis of Cobalt Silicides under Graphene Grown on Silicon Carbide. <i>Physics of the Solid State</i> , 2020 , 62, 519-528	0.8	2
343	Biplanar Epitaxial AlN/SiC/(n, p)SiC Structures for High-Temperature Functional Electronic Devices. <i>Technical Physics</i> , 2020 , 65, 428-433	0.5	1
342	Studying the Sensitivity of Graphene for Biosensor Applications. <i>Technical Physics Letters</i> , 2020 , 46, 462-465	0.7	2
341	Transformation of the buffer layer grown on 4H-SiC to single-layer graphene by ex situ hydrogen intercalation. <i>Fullerenes Nanotubes and Carbon Nanostructures</i> , 2020 , 28, 316-320	1.8	0

340	Comparison of graphene films grown on 6H-SiC and 4H-SiC substrates. <i>Fullerenes Nanotubes and Carbon Nanostructures</i> , 2020 , 28, 321-324	1.8	1
339	Development of the Processing Technique and Study of Microwave Switches Based on 4H-SiC p-n Diodes. <i>Technical Physics</i> , 2020 , 65, 250-253	0.5	
338	Terahertz Near-Field Response in Graphene Ribbons. <i>Technical Physics Letters</i> , 2020 , 46, 756-759	0.7	0
337	Raman scattering and low-frequency noise in epitaxial graphene chips. <i>Journal of Physics: Conference Series</i> , 2020 , 1697, 012130	0.3	1
336	Raman Studies of Graphene Films Grown on 4H-SiC Subjected to Deposition of Ni. <i>Semiconductors</i> , 2020 , 54, 1674-1677	0.7	
335	Comparative Study of Conventional and Quasi-Freestanding Epitaxial Graphenes Grown on 4H-SiC Substrate. <i>Semiconductors</i> , 2020 , 54, 1657-1660	0.7	
334	3C-SiC growth by sublimation in vacuum technology optimization. <i>Journal of Physics: Conference Series</i> , 2020 , 1697, 012070	0.3	
333	Raman and AFM studies of epitaxial graphene intended for manufacturing of transistors. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012018	0.3	0
332	Low-temperature quantum magnetotransport of graphene on SiC (0 0 0 1) in pulsed magnetic fields up to 30 T. <i>Journal of Physics Condensed Matter</i> , 2020 , 32, 115704	1.8	
331	Surface morphology control of the SiC (0001) substrate during the graphene growth. <i>Fullerenes Nanotubes and Carbon Nanostructures</i> , 2020 , 28, 281-285	1.8	2
330	Impact of 0.9 MeV electron irradiation on main properties of high voltage vertical power 4H-SiC MOSFETs. <i>Radiation Physics and Chemistry</i> , 2020 , 177, 109200	2.5	4
329	Investigation of epitaxial graphene via Raman spectroscopy: Origins of phonon mode asymmetries and line width deviations. <i>Carbon</i> , 2020 , 170, 666-676	10.4	5
328	Formation of Iron Silicides Under Graphene Grown on the Silicon Carbide Surface. <i>Physics of the Solid State</i> , 2020 , 62, 1944-1948	0.8	1
327	Effect Irradiation with 15 MeV Protons on Properties of 4H- SiC UV Detectors. <i>Materials Science Forum</i> , 2020 , 1004, 1104-1108	0.4	
326	Coulomb Electron Interaction between an Adsorbate and Substrate: a Model of a Surface Dimer. <i>Technical Physics Letters</i> , 2019 , 45, 924-926	0.7	
325	MoSe ₂ /graphene/6H-SiC heterojunctions: energy band diagram and photodegradation. <i>Semiconductor Science and Technology</i> , 2019 , 34, 125007	1.8	5
324	A Model of a Surface Dimer in the Problem of Adsorption. <i>Technical Physics Letters</i> , 2019 , 45, 461-463	0.7	3
323	Comparative Investigation of the Graphene-on-Silicon Carbide and CVD Graphene as a Basis for Biosensor Application. <i>Key Engineering Materials</i> , 2019 , 799, 185-190	0.4	1

322	Electrochemical Treatment of Graphene. <i>Key Engineering Materials</i> , 2019 , 799, 197-202	0.4	1
321	Role of the Carbon Sublattice in n-SiC Conductivity Compensation. <i>Journal of Surface Investigation</i> , 2019 , 13, 140-145	0.5	
320	Radiation Defects in Heterostructures 3C-SiC/4H-SiC. <i>Crystals</i> , 2019 , 9, 115	2.3	3
319	Effect of high energy (15 MeV) proton irradiation on vertical power 4H-SiC MOSFETs. <i>Semiconductor Science and Technology</i> , 2019 , 34, 045004	1.8	5
318	Cobalt Intercalation of Graphene on Silicon Carbide. <i>Physics of the Solid State</i> , 2019 , 61, 1316-1326	0.8	6
317	A Study of the Influence Exerted by Structural Defects on Photoluminescence Spectra in n-3C-SiC. <i>Technical Physics Letters</i> , 2019 , 45, 557-559	0.7	1
316	Studying the Formation of Single-Layer Graphene on the Surface of SiC. <i>Journal of Surface Investigation</i> , 2019 , 13, 395-399	0.5	
315	Low-Temperature Annealing of Lightly Doped n-4H-SiC Layers after Irradiation with Fast Electrons. <i>Semiconductors</i> , 2019 , 53, 975-978	0.7	3
314	Impact of High-Energy Electron Irradiation on Surge Currents in 4H-SiC JBS Schottky Diodes. <i>Semiconductors</i> , 2019 , 53, 1409-1413	0.7	
313	Electron Diffraction Study of Epitaxial Graphene Structure Grown upon SiC (0001) Thermal Destruction in Ar Atmosphere and in High Vacuum. <i>Physics of the Solid State</i> , 2019 , 61, 1940-1946	0.8	0
312	SiC-based electronics (100th anniversary of the Ioffe Institute). <i>Physics-Usppekhi</i> , 2019 , 62, 754-794	2.8	2
311	Raman spectroscopy estimation of the carrier concentration and the value of strain in monolayer graphene films grown on 4H-SiC. <i>Journal of Physics: Conference Series</i> , 2019 , 1400, 055037	0.3	1
310	Effect of Irradiation with 15-MeV Protons on Low Frequency Noise in Power SiC MOSFETs. <i>Semiconductors</i> , 2019 , 53, 1568-1572	0.7	2
309	Dependence of the Kinetics of Radiation-Induced Defect Formation on the Energy Absorbed by Si and SiC when Exposed to Fast Charged Particles. <i>Journal of Surface Investigation</i> , 2019 , 13, 1155-1159	0.5	3
308	Investigation of the Hydrogen Etching Effect of the SiC Surface on the Formation of Graphene Films. <i>Technical Physics</i> , 2019 , 64, 1843-1849	0.5	2
307	Electrophysical and Optical Properties of 4H-SiC UV Detectors Irradiated with Electrons. <i>Materials Science Forum</i> , 2019 , 963, 722-725	0.4	3
306	Dependence of the Carrier Removal Rate in 4H-SiC PN Structures on the Irradiation Temperature. <i>Materials Science Forum</i> , 2019 , 963, 730-733	0.4	1
305	Change in the Parameters of Electron-Irradiated 4H-SiC Schottky Diodes as a Function of the Time during Low-Temperature Isothermal Annealing. <i>Materials Science Forum</i> , 2019 , 963, 734-737	0.4	

304	Optical Estimation of the Carrier Concentration and the Value of Strain in Monolayer Graphene Grown on 4H-SiC. <i>Semiconductors</i> , 2019 , 53, 1904-1909	0.7	6
303	Characteristic features of the magnetoresistance related to structured defects in graphene on SiC (0001). <i>Materials Research Express</i> , 2019 , 6, 035603	1.7	
302	State memory in solution gated epitaxial graphene. <i>Applied Surface Science</i> , 2018 , 444, 36-41	6.7	2
301	Electrical and noise properties of proton irradiated 4H-SiC Schottky diodes. <i>Journal of Applied Physics</i> , 2018 , 123, 024502	2.5	16
300	Radiation Resistance of Devices Based on SiC. <i>Journal of Surface Investigation</i> , 2018 , 12, 364-369	0.5	3
299	Formation of Radiation Defects by Proton Braking in Lightly Doped n- and p-SiC Layers. <i>Semiconductors</i> , 2018 , 52, 310-315	0.7	2
298	Graphene/SiC Functionalization for Blood Type Sensing Applications. <i>Materials Science Forum</i> , 2018 , 924, 909-912	0.4	
297	Comparison of the Effects of Electron and Proton Irradiation on 4H-SiC and Si Device Structures. <i>Materials Science Forum</i> , 2018 , 924, 217-220	0.4	3
296	Intercalation of Iron Atoms under Graphene Formed on Silicon Carbide. <i>Physics of the Solid State</i> , 2018 , 60, 1439-1446	0.8	9
295	Effect of High Energy Electron Irradiation on Electrical and Noise Properties of 4H-SiC Schottky Diodes. <i>Materials Science Forum</i> , 2018 , 924, 605-608	0.4	
294	The Adaptive Behavior of the White Whales <i>Delphinapterus leucas</i> (Pallas, 1776) in the Southern Herd of the White Sea under Conditions of the Local Habitat During the Breeding Season. <i>Russian Journal of Marine Biology</i> , 2018 , 44, 58-67	0.7	0
293	Electron-Diffraction Study of the Structure of Epitaxial Graphene Grown by the Method of Thermal Destruction of 6H- and 4H-SiC (0001) in Vacuum. <i>Physics of the Solid State</i> , 2018 , 60, 1419-1424	0.8	1
292	Graphene on silicon carbide as a basis for gas- and biosensor applications. <i>Nanosystems: Physics, Chemistry, Mathematics</i> , 2018 , 95-97	1.8	2
291	Characterization of a porous silicon carbide layer produced on a 6H-SiC substrate: TEM (XHREM) and EDX studies 2018 , 73-78		
290	Study of properties and development of sensors based on graphene films grown on SiC (0001) by thermal destruction method. <i>Journal of Physics: Conference Series</i> , 2018 , 951, 012007	0.3	2
289	The Role of the Charge State of Surface Atoms of a Metal Substrate in Doping of Quasi-Free-Standing Graphene. <i>Technical Physics Letters</i> , 2018 , 44, 1089-1091	0.7	
288	Radiation-Induced Damage of Silicon-Carbide Diodes by High-Energy Particles. <i>Semiconductors</i> , 2018 , 52, 1758-1762	0.7	3
287	Field Effect in Monolayer Graphene Associated with the Formation of Graphene-Water Interface. <i>Physics of the Solid State</i> , 2018 , 60, 2668-2671	0.8	1

286	Electrical Properties of GaAs Nanowires Grown on Graphene/SiC Hybrid Substrates. <i>Semiconductors</i> , 2018 , 52, 1611-1615	0.7	2
285	Galvanic and Capacitive Effects in n-SiC Conductivity Compensation by Radiation-Induced Defects. <i>Semiconductors</i> , 2018 , 52, 1635-1637	0.7	
284	MBE growth of GaAs nanowires with modulated crystal structure. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 022043	0.3	
283	Kelvin probe microscopy of MoSe ₂ monolayers on graphene. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 081031	0.3	4
282	High Quality Graphene Grown by Sublimation on 4H-SiC (0001). <i>Semiconductors</i> , 2018 , 52, 1882-1885	0.7	6
281	Transition between Electron Localization and Antilocalization and Manifestation of the Berry Phase in Graphene on a SiC Surface. <i>Semiconductors</i> , 2018 , 52, 1616-1620	0.7	
280	Optical and electrical properties of the MoSe ₂ /graphene heterostructures. <i>Journal of Physics: Conference Series</i> , 2018 , 1092, 012002	0.3	4
279	MBE Growth and Structural Properties of GaP and InP Nanowires on a SiC Substrate with a Graphene Layer. <i>Semiconductors</i> , 2018 , 52, 1428-1431	0.7	2
278	Local Anodic Oxidation of Graphene Layers on SiC. <i>Technical Physics Letters</i> , 2018 , 44, 381-383	0.7	7
277	Impact of high energy electron irradiation on high voltage Ni/4H-SiC Schottky diodes. <i>Applied Physics Letters</i> , 2017 , 110, 083503	3.4	17
276	Effect of high energy electron irradiation on low frequency noise in 4H-SiC Schottky diodes. <i>Applied Physics Letters</i> , 2017 , 110, 133501	3.4	8
275	Degradation of 600-V 4H-SiC Schottky Diodes under Irradiation with 0.9 MeV Electrons. <i>Materials Science Forum</i> , 2017 , 897, 447-450	0.4	2
274	Effect of Neutron Irradiation on Current-Voltage Characteristics of Packaged Diodes Based on 6H-SiC pn Structures. <i>Materials Science Forum</i> , 2017 , 897, 459-462	0.4	3
273	Graphene Nanoribbons for Electronic Devices. <i>Annalen Der Physik</i> , 2017 , 529, 1700033	2.6	24
272	Field effects in graphene in an interface contact with aqueous solutions of acetic acid and potassium hydroxide. <i>Physics of the Solid State</i> , 2017 , 59, 2089-2091	0.8	1
271	Effect of the energy of bombarding electrons on the conductivity of n-4H-SiC (CVD) epitaxial layers. <i>Semiconductors</i> , 2017 , 51, 299-304	0.7	3
270	Radiation resistance of 4H-SiC Schottky diodes under irradiation with 0.9-MeV electrons. <i>Journal of Surface Investigation</i> , 2017 , 11, 924-926	0.5	4
269	Effects of irradiation with 8-MeV protons on n-3C-SiC heteroepitaxial layers. <i>Semiconductors</i> , 2017 , 51, 1044-1046	0.7	

268	Transport properties of graphene films grown by thermodestruction of SiC (0001) surface in argon medium. <i>Technical Physics Letters</i> , 2017 , 43, 849-852	0.7	2
267	A study of the effect of electron and proton irradiation on 4H-SiC device structures. <i>Technical Physics Letters</i> , 2017 , 43, 1027-1029	0.7	4
266	Study of the crystal and electronic structure of graphene films grown on 6H-SiC (0001). <i>Semiconductors</i> , 2017 , 51, 1072-1080	0.7	33
265	Radiation Effects in Silicon Carbide. <i>Materials Research Foundations</i> , 2017 ,	1.3	13
264	Graphene-based biosensors. <i>Technical Physics Letters</i> , 2016 , 42, 729-732	0.7	14
263	2016 ,		7
262	Transport properties of graphene in the region of its interface with water surface. <i>Physics of the Solid State</i> , 2016 , 58, 1483-1486	0.8	2
261	Anomalous Scatter of Forward Current-Voltage Characteristics of He ⁺ -Irradiated Ni/4H-SiC Schottky Diodes. <i>Materials Science Forum</i> , 2016 , 858, 749-752	0.4	6
260	Development of a spinodal decomposition model for the example of a heterostructure based on silicon carbide polytypes. <i>Technical Physics Letters</i> , 2016 , 42, 1153-1155	0.7	
259	Electron-diffraction study of graphene-film growth stages during the thermal destruction of 6H-SiC (000(bar 1)) in vacuum. <i>Semiconductors</i> , 2016 , 50, 951-956	0.7	
258	Effect of recoil atoms on radiation-defect formation in semiconductors under 110-MeV proton irradiation. <i>Journal of Surface Investigation</i> , 2016 , 10, 693-697	0.5	4
257	Supersensitive graphene-based gas sensor. <i>Technical Physics</i> , 2016 , 61, 453-457	0.5	14
256	Effect of the energy of recoil atoms on conductivity compensation in moderately doped n-Si and n-SiC under irradiation with MeV electrons and protons. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2016 , 384, 100-105	1.2	6
255	Long-term environmental impact of an oil spill in the southern part of Onega Bay, the White Sea. <i>Russian Journal of Marine Biology</i> , 2016 , 42, 205-215	0.7	4
254	On the electronic state of an atom adsorbed on epitaxial graphene formed on metallic and semiconductor substrates. <i>Physics of the Solid State</i> , 2015 , 57, 213-218	0.8	1
253	Role of the recoil atom energy in the formation of radiation-induced defects in semiconductors under electron bombardment. <i>Journal of Surface Investigation</i> , 2015 , 9, 231-236	0.5	9
252	Irradiation of 4H-SiC UV detectors with heavy ions. <i>Semiconductors</i> , 2015 , 49, 540-546	0.7	13
251	Radiation hardness of n-GaN schottky diodes. <i>Semiconductors</i> , 2015 , 49, 1341-1343	0.7	2

250	Model for conductivity compensation of moderately doped n- and p-4H-SiC by high-energy electron bombardment. <i>Journal of Applied Physics</i> , 2015 , 117, 155702	2.5	22
249	Conductivity Compensation in CVD-Grown n-4H-SiC under Irradiation with 0.9 MeV Electrons. <i>Materials Science Forum</i> , 2015 , 821-823, 293-296	0.4	0
248	Characterization of 4H-SiC pn Structures with Unstable Excess Current. <i>Materials Science Forum</i> , 2015 , 821-823, 648-651	0.4	
247	RHEED Study of Epitaxial Graphene on Conductive and Semi-Insulating 6H-SiC (0001) Substrates. <i>Materials Science Forum</i> , 2015 , 821-823, 945-948	0.4	1
246	Effect of irradiation with MeV protons and electrons on the conductivity compensation and photoluminescence of moderately doped p-4H-SiC (CVD). <i>Semiconductors</i> , 2015 , 49, 1163-1165	0.7	10
245	On the relationship between radiation-stimulated photoluminescence and nitrogen atoms in p-4H-SiC. <i>Technical Physics Letters</i> , 2015 , 41, 1143-1145	0.7	
244	Radiation-stimulated photoluminescence in electron irradiated 4H-SiC. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 485106	3	16
243	Fabrication of quasi-superlattices at the interface between 3C-SiC epitaxial layer and substrates of hexagonal SiC polytypes by sublimation epitaxy in vacuum. <i>Technical Physics Letters</i> , 2015 , 41, 1156-1158	0.7	4
242	Size confinement effect in graphene grown on 6H-SiC (0001) substrate. <i>Carbon</i> , 2015 , 86, 139-145	10.4	10
241	Conductivity compensation in n-4H-SiC (CVD) under irradiation with 0.9-MeV electrons. <i>Semiconductors</i> , 2014 , 48, 1006-1009	0.7	9
240	Irradiation of sublimation-grown p-SiC with 0.9-MeV electrons. <i>Technical Physics Letters</i> , 2014 , 40, 651-652	0.7	1
239	Variant of Excess Current in 4H-SiC pn Structures. <i>Materials Science Forum</i> , 2014 , 778-780, 859-862	0.4	3
238	On the self-structuring of single-crystal silicon wafers under inductive heating in vacuum. <i>Semiconductors</i> , 2014 , 48, 350-353	0.7	
237	On the possibility of spinodal decomposition in the transition layer of a heterostructure based on silicon-carbide polytypes. <i>Semiconductors</i> , 2014 , 48, 701-704	0.7	
236	Evaluation of the effect of adsorption on the conductivity of single-layer graphene formed on a semiconductor substrate. <i>Physics of the Solid State</i> , 2014 , 56, 2580-2583	0.8	2
235	Nonlinear effects in semiconductor-conductivity compensation by radiation defects. <i>Journal of Surface Investigation</i> , 2014 , 8, 950-952	0.5	8
234	Comparison of the radiation hardness of silicon and silicon carbide. <i>Semiconductors</i> , 2014 , 48, 1293-1295	0.7	6
233	Irradiation and annealing of p-type silicon carbide 2014 ,		1

232	A Study of the Intermediate Layer in 3C-SiC/6H-SiC Heterostructures. <i>Materials Science Forum</i> , 2014 , 778-780, 247-250	0.4	
231	A study of the intermediate layer in 3C _B SiC/6H _B SiC heterostructures. <i>Journal of Crystal Growth</i> , 2014 , 396, 100-103	1.6	3
230	Comparative study of 3C-SiC layers sublimation-grown on a 6H-SiC substrate. <i>Semiconductors</i> , 2013 , 47, 1267-1270	0.7	1
229	Investigation of the transition layer in 3C-SiC/6H-SiC heterostructures. <i>Semiconductors</i> , 2013 , 47, 1539-1543	0.7	3
228	Optical Characterization of Compensating Defects in Cubic SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 401-404	0.4	
227	Temperature Dependence of the Band-Edge Injection Electroluminescence of 4H-SiC pn Structure. <i>Materials Science Forum</i> , 2013 , 740-742, 569-572	0.4	2
226	Structure and transport properties of nanocarbon films prepared by sublimation on a 6H-SiC surface. <i>Semiconductors</i> , 2013 , 47, 301-306	0.7	10
225	P-6H-SiC Conductivity Compensation after Irradiation of 8MeV Protons. <i>Materials Science Forum</i> , 2013 , 740-742, 353-356	0.4	
224	Comparative Analysis of Defect Formation in Silicon Carbide under Electron and Proton Irradiation. <i>Materials Science Forum</i> , 2013 , 740-742, 369-372	0.4	
223	Heteroepitaxial Growth of 3C-SiC on Polar Faces of 6H-SiC Substrates, TEM Investigations. <i>Materials Science Forum</i> , 2013 , 740-742, 267-270	0.4	2
222	Selective 4H-SiC UV Detectors. <i>Materials Science Forum</i> , 2013 , 740-742, 1014-1017	0.4	
221	To the Experimental Determination of the Spontaneous Polarization for the Silicon Carbide Polytypes. <i>Materials Science Forum</i> , 2013 , 740-742, 459-462	0.4	
220	Energy Gaps Induced by a Semiconducting Substrate in the Epitaxial Graphene Density of States. <i>Materials Science Forum</i> , 2013 , 740-742, 141-144	0.4	0
219	Low-Temperature Transport Properties of Graphene and Multilayer Graphene on 6H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 137-140	0.4	3
218	Radiation hardness of a wide-bandgap material by the example of SiC nuclear radiation detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2012 , 675, 20-23	1.2	3
217	Similarities and distinctions of defect production by fast electron and proton irradiation: Moderately doped silicon and silicon carbide of n-type. <i>Semiconductors</i> , 2012 , 46, 456-465	0.7	26
216	On the possibility of the experimental determination of spontaneous polarization for silicon carbide polytypes. <i>Semiconductors</i> , 2012 , 46, 913-916	0.7	1
215	Radiation resistance of wide-gap materials as exemplified by SiC nuclear radiation detectors. <i>Technical Physics</i> , 2012 , 57, 556-560	0.5	2

214	Annealing of radiation-compensated silicon carbide. <i>Technical Physics Letters</i> , 2012 , 38, 910-912	0.7	2
213	Transport Properties of Multi-Graphene Films Grown on Semi-Insulating SiC. <i>Fullerenes Nanotubes and Carbon Nanostructures</i> , 2012 , 20, 553-557	1.8	1
212	Radiation Hardness of Wide-Bandgap Materials as Exemplified by SiC Nuclear Radiation Detectors. <i>Materials Science Forum</i> , 2012 , 717-720, 549-552	0.4	
211	Epitaxial Single-Layer Graphene on the SiC Substrate. <i>Materials Science Forum</i> , 2012 , 717-720, 645-648	0.4	1
210	Energy distribution of recoil atoms and formation of radiation defects in silicon carbide films under proton irradiation. <i>Semiconductors</i> , 2011 , 45, 141-144	0.7	1
209	Low-temperature transport properties of multigraphene films grown on the SiC surface by sublimation. <i>Semiconductors</i> , 2011 , 45, 623-627	0.7	14
208	Vacancy model of micropipe annihilation in epitaxial silicon carbide layers. <i>Semiconductors</i> , 2011 , 45, 727-730	0.7	3
207	Fabrication of improved-quality seed crystals for growth of bulk silicon carbide. <i>Semiconductors</i> , 2011 , 45, 828-831	0.7	1
206	Conductivity compensation in p-6H-SiC in irradiation with 8-MeV protons. <i>Semiconductors</i> , 2011 , 45, 1145-1147	0.7	2
205	On the problem of the radiation hardness of SiC nuclear radiation detectors at high working temperatures. <i>Semiconductors</i> , 2011 , 45, 1369-1373	0.7	4
204	Structure and characteristics of the high-temperature SiC detectors based on Al ion-implanted p+n junctions. <i>Semiconductor Science and Technology</i> , 2011 , 26, 045001	1.8	8
203	Formation of Periodic Steps on 6H-SiC (0001) Surface by Annealing in a High Vacuum. <i>Materials Science Forum</i> , 2011 , 679-680, 437-440	0.4	9
202	Uniformity of Properties of 4H-SiC CVD Films under Exposure to Radiation. <i>Materials Science Forum</i> , 2011 , 679-680, 177-180	0.4	
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200	Fabrication and Use of Atomically Smooth Steps on 6H-SiC for Calibration of z-Displacements in Scanning Probe Microscopy. <i>Materials Science Forum</i> , 2010 , 645-648, 767-770	0.4	1
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198	Impact Ionization in 4H-SiC Nuclear Radiation Detectors. <i>Materials Science Forum</i> , 2010 , 645-648, 1077-1080	0.4	1
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192	Electrical characteristics of multigraphene films grown on high-resistivity silicon carbide substrates. <i>Semiconductors</i> , 2010 , 44, 1389-1391	0.7	4
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189	Use of sublimation epitaxy for obtaining volume 3C-SiC crystals. <i>Technical Physics Letters</i> , 2010 , 36, 574-576		
188	Energy characteristics of SiC(0001)-intercalated hydrogen-graphene system. <i>Technical Physics Letters</i> , 2010 , 36, 856-858	0.7	3
187	Effect of electron irradiation on carrier removal rate in silicon and silicon carbide with 4H modification 2010 , 42, 242		
186	Effect of electron and proton irradiation on characteristics of SiC surface-barrier detectors of nuclear radiation 2010 , 42, 363		
185	Heat-Resistant Barrier Contacts Made on the Basis of TiBx and ZrBx to SiC and GaN. <i>Materials Science Forum</i> , 2009 , 615-617, 565-568	0.4	1
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181	Operation of Al-Implanted SiC Nuclear Detectors Subjected to High Radiation Fluences at Temperatures of up to 250 °C. <i>Materials Science Forum</i> , 2009 , 615-617, 853-856	0.4	
180	An Effective Method of Characterization of SiC Substrates. <i>Materials Science Forum</i> , 2009 , 615-617, 279-282		
179	4H-SiC Nuclear Radiation p-n Detectors for Operation up to Temperature 375 °C. <i>Materials Science Forum</i> , 2009 , 615-617, 849-852	0.4	3

178	Far-Action Radiation Defects and Gettering Effects in 4H-SiC Implanted with Al Ions. <i>Materials Science Forum</i> , 2009 , 615-617, 473-476	0.4	3
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43	Structural and Optical Studies of Low-Doped n-6H SiC Layers Grown by Vacuum Sublimation. <i>Materials Science Forum</i> , 2000 , 338-342, 509-512	0.4	3
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39	Doping of n-type 6H-SiC and 4H-SiC with defects created with a proton beam. <i>Journal of Applied Physics</i> , 2000 , 88, 6265-6271	2.5	88
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35	Influence of native defects on polytypism in SiC. <i>Semiconductors</i> , 1999 , 33, 707-709	0.7	9

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23	Photoluminescence of anodized silicon carbide. <i>Semiconductors</i> , 1997 , 31, 202-203	0.7	2
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20	6H-3C SiC structures grown by sublimation epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 46, 168-170	3.1	1
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18	A study of the contact potential difference in p-n 6H-SiC structures grown by various techniques. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 46, 271-274	3.1	
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